

Notice of References Cited	Application/Control No. 10/620,430	Applicant(s)/Patent Under Reexamination INOUE ET AL.	
	Examiner Belur V Keshavan	Art Unit 2825	Page 1 of 1

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*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Name	Classification
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	C	US-6,548,333	04-2003	Smith, Richard Peter	438/172
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NON-PATENT DOCUMENTS

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	V	Sullivan et al., High-Power 10 GHz operation of AlGaIn HFETs on insulating SiC, IEEE Elect. Device Letters, Vol. 19, No 6, 1998
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*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)
Dates in MM-YYYY format are publication dates. Classifications may be US or foreign.